

2N7000 / 2N7002 / NDS7002A N-Channel Enhancement Mode Field Effect Transistor

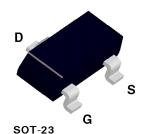
General Description

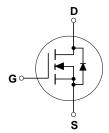
These N-Channel enhancement mode field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 400mA DC and can deliver pulsed currents up to 2A. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

Features

- High density cell design for low R_{DS(ON)}.
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.







Absolute Maximum Ratings T = 25°C unless otherwise noted

Symbol	Parameter	2N7000	2N7002	NDS7002A	Units			
V _{DSS}	Drain-Source Voltage		60					
V_{DGR}	Drain-Gate Voltage ($R_{GS} \le 1 M\Omega$)		60		V			
V_{GSS}	Gate-Source Voltage - Continuous		±20		V			
	- Non Repetitive (tp < 50μs)		±40					
I _D	Maximum Drain Current - Continuous	200	115	280	mA			
	- Pulsed	500	800	1500				
P_{D}	Maximum Power Dissipation	400	200	300	mW			
	Derated above 25°C	3.2	1.6	2.4	mW/°C			
T _J ,T _{STG}	Operating and Storage Temperature Range	-55	to 150	-65 to 150	°C			
T _L	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds		300		°C			
THERMA	L CHARACTERISTICS				•			
R _{θJA}	Thermal Resistance, Junction-to-Ambient	312.5	625	417	°C/W			

Symbol	Parameter	Conditions	Type	Min	Тур	Max	Units	
OFF CHA	RACTERISTICS							
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 10 \mu\text{A}$		All	60			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$		2N7000			1	μΑ
			T _J =125°C				1	mA
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$		2N7002			1	μΑ
			T _J =125°C	NDS7002A			0.5	mA
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 15 \text{ V}, V_{DS} = 0 \text{ V}$		2N7000			10	nA
		$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$		2N7002 NDS7002A			100	nA
GSSR	Gate - Body Leakage, Reverse	$V_{GS} = -15 \text{ V}, V_{DS} = 0 \text{ V}$		2N7000			-10	nA
		$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$		2N7002 NDS7002A			-100	nA
ON CHAF	RACTERISTICS (Note 1)							
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	2N7000	0.8	2.1	3	V	
		$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2N7002 NDS7002A	1	2.1	2.5	
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_{D} = 500 \text{ mA}$		2N7000		1.2	5	Ω
			T _J =125°C			1.9	9	
		$V_{GS} = 4.5 \text{ V}, I_{D} = 75 \text{ mA}$				1.8	5.3	
		$V_{GS} = 10 \text{ V}, I_{D} = 500 \text{ mA}$		2N7002		1.2	7.5	
			T _J =100°C			1.7	13.5	
		$V_{GS} = 5.0 \text{ V}, I_{D} = 50 \text{ mA}$				1.7	7.5	
			T _J =100C			2.4	13.5	
		$V_{GS} = 10 \text{ V}, I_{D} = 500 \text{ mA}$		NDS7002A		1.2	2	
			T _J =125°C			2	3.5	
		$V_{GS} = 5.0 \text{ V}, I_{D} = 50 \text{ mA}$				1.7	3	
			T _J =125°C			2.8	5	
/ _{DS(ON)}	Drain-Source On-Voltage	$V_{GS} = 10 \text{ V}, I_{D} = 500 \text{ mA}$		2N7000		0.6	2.5	V
		$V_{GS} = 4.5 \text{ V}, I_{D} = 75 \text{ mA}$				0.14	0.4	
		$V_{GS} = 10 \text{ V}, I_{D} = 500 \text{mA}$		2N7002		0.6	3.75	
		$V_{GS} = 5.0 \text{ V}, I_{D} = 50 \text{ mA}$			0.09	1.5		
		$V_{GS} = 10 \text{ V}, I_{D} = 500 \text{mA}$	NDS7002A		0.6	1		
		$V_{GS} = 5.0 \text{ V}, I_{D} = 50 \text{ mA}$			0.09	0.15	1	

Symbol	Parameter	Туре	Min	Тур	Max	Units	
ON CHAP	RACTERISTICS Continued (Note 1)	•					
I _{D(ON)}	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, \ V_{DS} = 10 \text{ V}$	2N7000	75	600		mA
		$V_{GS} = 10 \text{ V}, V_{DS} \ge 2 V_{DS(on)}$	2N7002	500	2700		
		$V_{GS} = 10 \text{ V}, V_{DS} \ge 2 V_{DS(on)}$	NDS7002A	500	2700		
g _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 200 mA	2N7000	100	320		mS
		$V_{DS} \ge 2 V_{DS(on)}, I_{D} = 200 \text{ mA}$	2N7002	80	320		
		$V_{DS} \ge 2 V_{DS(on)}$, $I_D = 200 \text{ mA}$	NDS7002A	80	320		
DYNAMIC	CHARACTERISTICS						
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, \ V_{GS} = 0 \text{ V}, $ f = 1.0 MHz	All		20	50	pF
C _{oss}	Output Capacitance	f = 1.0 MHz	All		11	25	pF
C _{rss}	Reverse Transfer Capacitance		All		4	5	pF
t _{on} Turn-C	Turn-On Time	$V_{DD} = 15 \text{ V}, R_{L} = 25 \Omega,$ $I_{D} = 500 \text{ mA}, V_{GS} = 10 \text{ V},$ $R_{GEN} = 25$	2N7000			10	ns
		$\begin{split} &V_{DD} = 30 \; V, \; R_{L} = 150 \; \Omega, \\ &I_{D} = 200 \; mA, \; V_{GS} = 10 \; V, \\ &R_{GEN} = 25 \; \Omega \end{split}$	2N700 NDS7002A			20	
t _{off}	Turn-Off Time	$V_{DD} = 15 \text{ V}, R_{L} = 25 \Omega,$ $I_{D} = 500 \text{ mA}, V_{GS} = 10 \text{ V},$ $R_{GEN} = 25$	2N7000			10	ns
		$\begin{aligned} & V_{\text{DD}} = 30 \text{ V}, \text{ R}_{\text{L}} = 150 \Omega, \\ & I_{\text{D}} = 200 \text{ mA}, V_{\text{GS}} = 10 \text{ V}, \\ & R_{\text{GEN}} = 25 \Omega \end{aligned}$	2N700 NDS7002A			20	
DRAIN-S	OURCE DIODE CHARACTERISTICS	S AND MAXIMUM RATINGS					
I _s	Maximum Continuous Drain-Sour	2N7002			115	mA	
			NDS7002A			280	
I _{SM}	Maximum Pulsed Drain-Source D	iode Forward Current	2N7002			0.8	Α
			NDS7002A	·		1.5	
V _{SD}	Drain-Source Diode Forward	$V_{GS} = 0 \text{ V}, I_{S} = 115 \text{ mA} \text{ (Note 1)}$	2N7002		0.88	1.5	V
	Voltage	V _{GS} = 0 V, I _S = 400 mA (Note 1)	NDS7002A		0.88	1.2	1

Note: 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

2N7000 / 2N7002 / NDS7002A

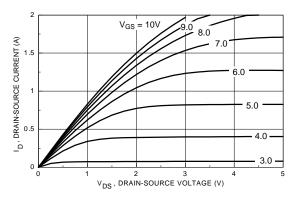


Figure 1. On-Region Characteristics

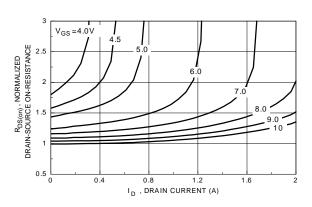


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

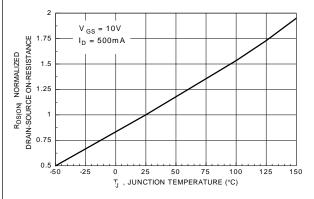


Figure 3. On-Resistance Variation with Temperature

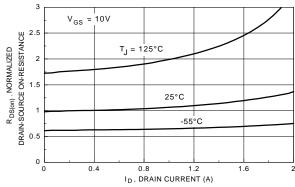


Figure 4. On-Resistance Variation with Drain Current and Temperature

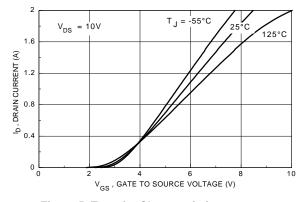


Figure 5. Transfer Characteristics

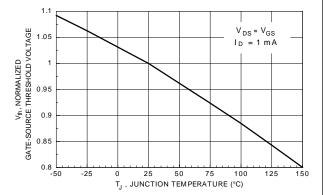


Figure 6. Gate Threshold Variation with Temperature

Typical Electrical Characteristics (continued)

2N7000 / 2N7002 /NDS7002A

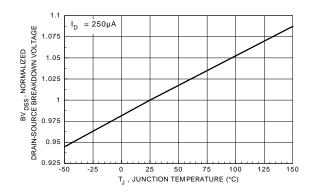
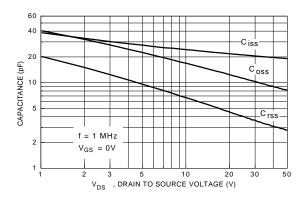


Figure 7. Breakdown Voltage Variation with Temperature

Figure 8. Body Diode Forward Voltage Variation with



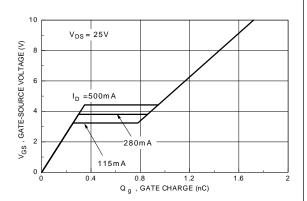
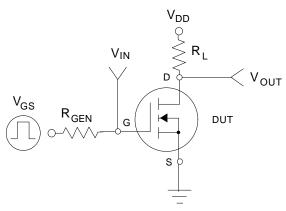


Figure 9. Capacitance Characteristics

Figure 10. Gate Charge Characteristics



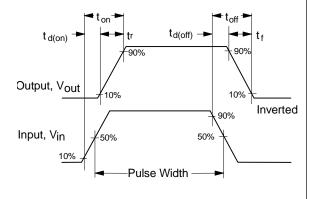
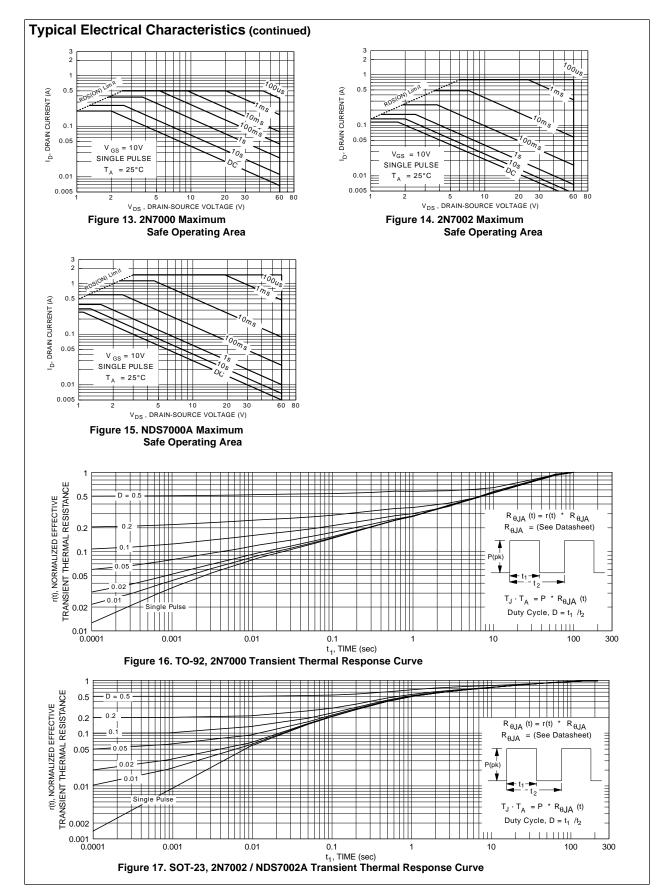
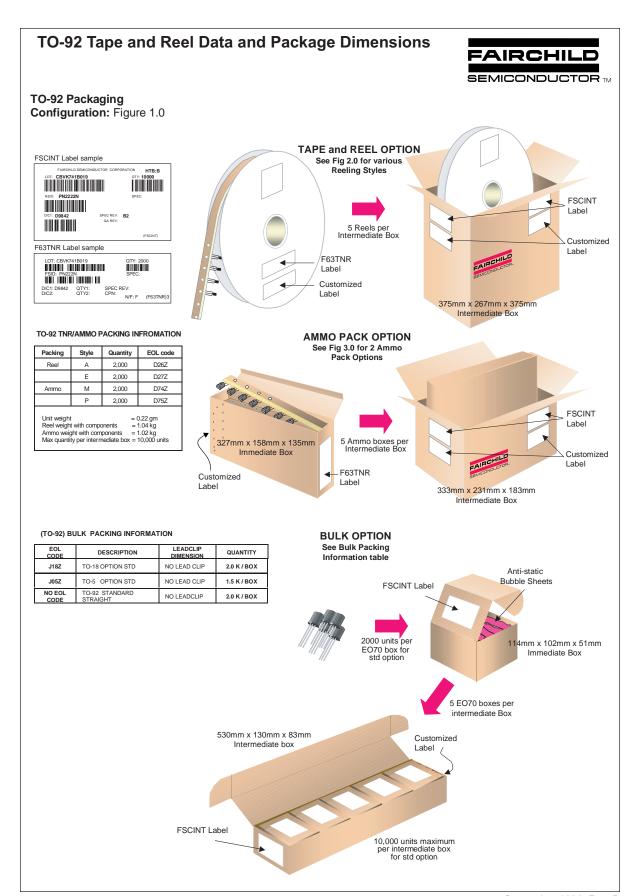


Figure 11.

Figure 12. Switching Waveforms

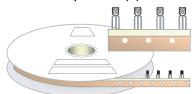




TO-92 Tape and Reel Data and Package Dimensions, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

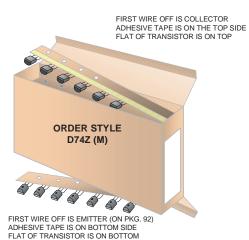


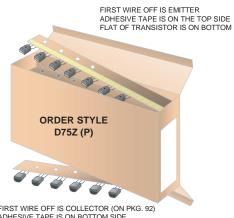
Style "A", D26Z, D70Z (s/h)

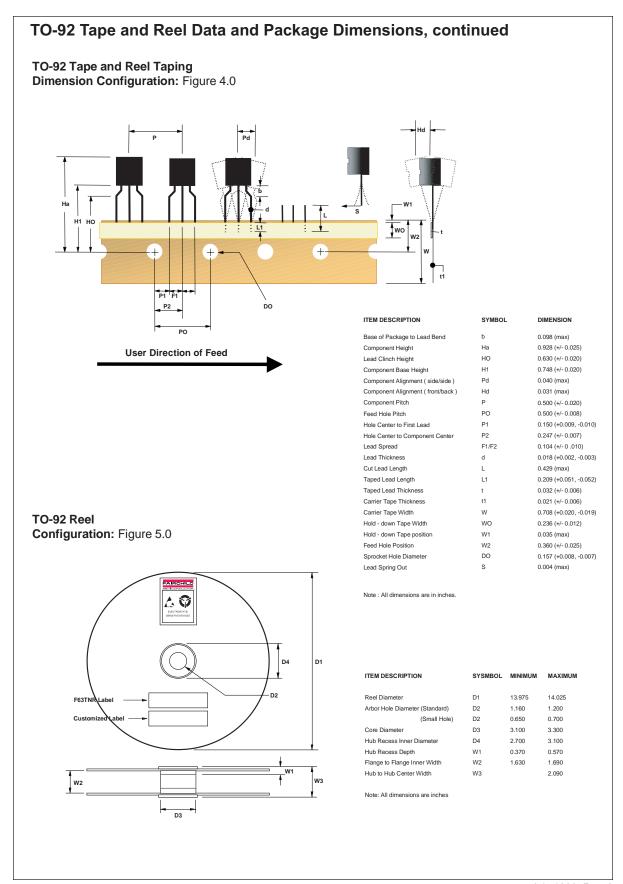
Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0

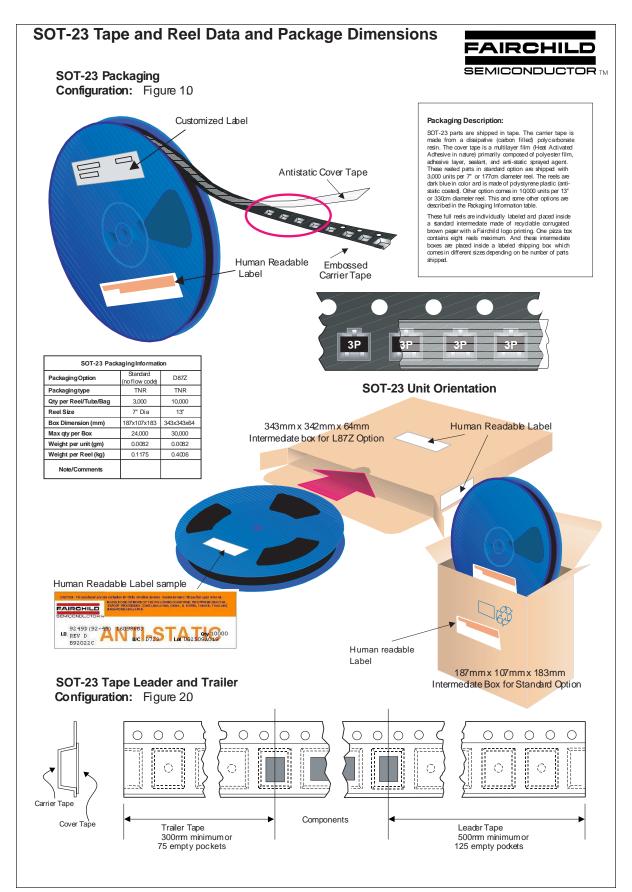






TO-92 Tape and Reel Data and Package Dimensions TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 96 94 В В 0.76 В G Ε Ø0.060 [Ø1.52] 0.010 [0.254] DEEP В S С 0.615 0.570 5.0°TYP.

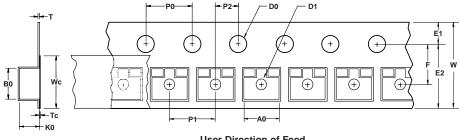
January 2000, Rev. B



SOT-23 Tape and Reel Data and Package Dimensions, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



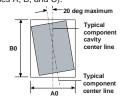
User Direction of Feed	

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



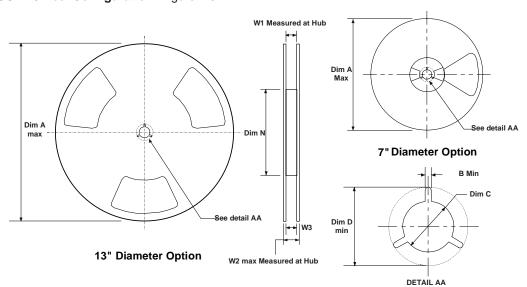
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

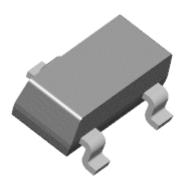
SOT-23 Reel Configuration: Figure 4.0

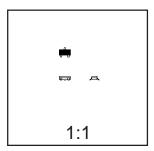


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

SOT-23 Tape and Reel Data and Package Dimensions, continued

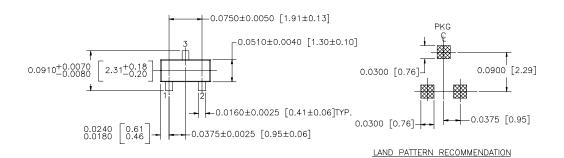
SOT-23 (FS PKG Code 49)

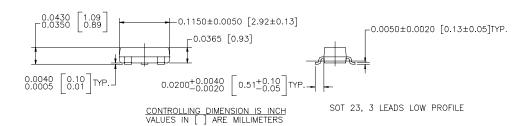




Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Definition of Terms

Datasheet Identification	Product Status	Definition
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